

IRLD014 Information

Part Number IRLD014

Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 60V 1.7A 4-DIP

Package 4-DIP (0.300", 7.62mm)

For the pricing/inventory/lead time, please contact

Website: https://www.heisener.com

E-mail: salesdept@heisener.com



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Certified Quality

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IRLD014 Specifications

For Reference Only

Manufacturer Part Number IRLD014 Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 4-DIP (0.300", 7.62mm) Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 1.7A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4V, 5V Vgs(th) (Max) @ Id 2V @ 250µA Gate Charge (Qg) (Max) @ Vgs 8.4nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 400pF @ 25V Vgs (Max) 4 00pF @ 25V Vgs (Max) 2 00mF @ 14, 5V Power Dissipation (Max) 1.3W (Ta) Rds On (Max) @ Id, Vgs 200 mOhm @ 1A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package 4-DIP, Hexdip, HVMDIP Package / Case 4-DIP, Hexdip, HVMDIP		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 4-DIP (0.300", 7.62mm) Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Orain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 1.7A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Qate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Quench Charge (Qg) month (Max) Rds On (Max) @ Id, Vgs Poperating Temperature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Through Hole Supplier Device Package 4-DIP (Ho.300", 7.62mm)	Manufacturer Part Number	IRLD014
Package 4-DIP (0.300", 7.62mm) Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 1.7A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4V, 5V Vgs(th) (Max) @ Id 2V @ 250μA Gate Charge (Qg) (Max) @ Vgs 8.4nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 400pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 1.3W (Ta) Rds On (Max) @ Id, Vgs 200 mOhm @ 1A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package 4-DIP, Hexdip, HVMDIP Package / Case 4-DIP (0.300", 7.62mm)	Manufacturer	Vishay Siliconix
Package 4-DIP (0.300", 7.62mm) Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 1.7A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4V, 5V Vgs(th) (Max) @ Id 2V @ 250μA Gate Charge (Qg) (Max) @ Vgs 8.4nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 400pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 1.3W (Ta) Rds On (Max) @ Id, Vgs 200 mOhm @ 1A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package 4-DIP, Hexdip, HVMDIP Package / Case 4-DIP (0.300", 7.62mm)	Category	Discrete Semiconductor Products
Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 1.7A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4V, 5V Vgs(th) (Max) @ Id 2V @ 250µA Gate Charge (Qg) (Max) @ Vgs 8.4nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 400pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 1.3W (Ta) Rds On (Max) @ Id, Vgs 200 mOhm @ 1A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package 4-DIP, Hexdip, HVMDIP Package / Case 4-DIP (0.300", 7.62mm)		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C1.7A (Ta)Drive Voltage (Max Rds On, Min Rds On)4V, 5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs8.4nC @ 5VInput Capacitance (Ciss) (Max) @ Vds400pF @ 25VVgs (Max)±10VFET Feature-Power Dissipation (Max)1.3W (Ta)Rds On (Max) @ Id, Vgs200 mOhm @ 1A, 5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device Package4-DIP, Hexdip, HVMDIPPackage / Case4-DIP (0.300", 7.62mm)	Package	4-DIP (0.300", 7.62mm)
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C1.7A (Ta)Drive Voltage (Max Rds On, Min Rds On)4V, 5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs8.4nC @ 5VInput Capacitance (Ciss) (Max) @ Vds400pF @ 25VVgs (Max)±10VFET Feature-Power Dissipation (Max)1.3W (Ta)Rds On (Max) @ Id, Vgs200 mOhm @ 1A, 5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device Package4-DIP, Hexdip, HVMDIPPackage / Case4-DIP (0.300", 7.62mm)	Series	-
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C1.7A (Ta)Drive Voltage (Max Rds On, Min Rds On)4V, 5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs8.4nC @ 5VInput Capacitance (Ciss) (Max) @ Vds400pF @ 25VVgs (Max)±10VFET Feature-Power Dissipation (Max)1.3W (Ta)Rds On (Max) @ Id, Vgs200 mOhm @ 1A, 5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device Package4-DIP, Hexdip, HVMDIPPackage / Case4-DIP (0.300", 7.62mm)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Rough (Ciss) (Max) @ Vds Vgs (Max) Vgs (Max) Vgs (Max) Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 1.7A (Ta) 1.7A (Ta) 1.7A (Ta) 1.7A (Ta) 1.7A (Ta) 4V, 5V 1.7V 2V @ 250µA 400pF @ 25V 400pF @ 25V 400pF @ 25V 400pF @ 25V 20V 400pF @ 25V 20V 400pF @ 25V 400pF	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4V, 5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs8.4nC @ 5VInput Capacitance (Ciss) (Max) @ Vds400pF @ 25VVgs (Max)±10VFET Feature-Power Dissipation (Max)1.3W (Ta)Rds On (Max) @ Id, Vgs200 mOhm @ 1A, 5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device Package4-DIP, Hexdip, HVMDIPPackage / Case4-DIP (0.300", 7.62mm)	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id	Current - Continuous Drain (Id) @ 25°C	1.7A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 400pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 200 mOhm @ 1A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package 4-DIP, Hexdip, HVMDIP Package / Case 4-DIP (0.300", 7.62mm)	Drive Voltage (Max Rds On, Min Rds On)	4V, 5V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±10V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 200 mOhm @ 1A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package 4-DIP, Hexdip, HVMDIP Package / Case 4-DIP (0.300", 7.62mm)	Vgs(th) (Max) @ Id	2V @ 250μA
Vgs (Max)±10VFET Feature-Power Dissipation (Max)1.3W (Ta)Rds On (Max) @ Id, Vgs200 mOhm @ 1A, 5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device Package4-DIP, Hexdip, HVMDIPPackage / Case4-DIP (0.300", 7.62mm)	Gate Charge (Qg) (Max) @ Vgs	8.4nC @ 5V
FET Feature - Power Dissipation (Max) 1.3W (Ta) Rds On (Max) @ Id, Vgs 200 mOhm @ 1A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package 4-DIP, Hexdip, HVMDIP Package / Case 4-DIP (0.300", 7.62mm)	Input Capacitance (Ciss) (Max) @ Vds	400pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 200 mOhm @ 1A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package 4-DIP, Hexdip, HVMDIP Package / Case 4-DIP (0.300", 7.62mm)	Vgs (Max)	±10V
Rds On (Max) @ Id, Vgs200 mOhm @ 1A, 5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device Package4-DIP, Hexdip, HVMDIPPackage / Case4-DIP (0.300", 7.62mm)	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package 4-DIP, Hexdip, HVMDIP Package / Case 4-DIP (0.300", 7.62mm)	Power Dissipation (Max)	1.3W (Ta)
Mounting Type Through Hole Supplier Device Package 4-DIP, Hexdip, HVMDIP Package / Case 4-DIP (0.300", 7.62mm)	Rds On (Max) @ Id, Vgs	200 mOhm @ 1A, 5V
Supplier Device Package 4-DIP, Hexdip, HVMDIP Package / Case 4-DIP (0.300", 7.62mm)	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case 4-DIP (0.300", 7.62mm)	Mounting Type	Through Hole
	Supplier Device Package	4-DIP, Hexdip, HVMDIP
Report errors?	Package / Case	4-DIP (0.300", 7.62mm)
		Report errors?

IRLD014 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRLD014 Payment Methods





















IRLD014 Shipping Methods













If you have any question about IRLD014, please do not hesitate to contact us!

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